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CLAIMS 1-5. (CANCELLED)

CLAIMS 6-9. (CANCELLED)

10. In the fabrication of organic thin film field effect semiconductor devices wherein there is an n-channel having source and drain contacts separated by said n-channel, an improvement for producing high electron mobility in said n-channel without treatment of the interface between said contacts and said organic thin film characterized by, said organic thin film being a compound with a N,N"-di(n-1H, 1H-perfluorooctyl) perylene 3,4,9,10- tetracarboxylic acid diimide structure.

11. The improvement of claim 10 wherein in said thin film field effect semiconductor devices there is a substrate with a gate electrode that is covered by a gate dielectric ,

said source and drain electrodes are positioned in contact with said gate dielectric and aligned with said gate, and, said thin film field effect devices being characterized by having an organic thin film semiconductor member of a compound having an N,N"-di(n-1H, 1H-perfluorooctyl) perylene 3,4,9,10- tetracarboxylic acid diimide structure extending over said source and drain electrodes and in contact with said gate dielectric.

12. The improvement of claim 10 wherein in said thin film field effect semiconductor devices there is a substrate with a gate electrode that is covered by a gate dielectric, said devices being characterized by having an organic thin film semiconductor member of a compound having an N,N"-di(n-1H, 1H-perfluorooctyl) perylene 3,4,9,10- tetracarboxylic acid diimide structure positioned in contact with and extending over said gate dielectric, and, source and drain electrodes positioned in contact with said organic thin film semiconductor member and aligned with said gate.